

**Overview**

CST816D self-capacitive touch chip, using high-speed MCU core and embedded DSP circuit, combined with its own fast self-capacitive sensing technology, can widely support a variety of self-capacitive patterns including triangles, on which single-point gestures and real two-point operations are realized, achieving extremely high sensitivity and low standby power.

Chip Features

• Built-in fast self-capacitance detection circuit and high-performance DSP module

• Support online programming; •

Built-in watchdog; • Support

multiple buttons; • Support standby

gesture wake-up function;

• Capacitive screen support

• Supports up to 13 sensing channels; • Supports

channel suspension/pull-down design; • Automatic

adjustment of module parameters;

• Performance indicators

• Refresh rate > 100Hz; • Single-point

gesture and real two-point operation;

• Power consumption index

• Typical power consumption in dynamic mode is 4mA;

• Typical power consumption in sleep mode is 8uA;

• Communication interface

• I2C master/slave communication interface, rate 10KHz~400KHz

Configurable;

• Compatible with 1.8V/3.3V interface levels.

• Power supply

• Single power supply 2.8V ~ 3.6V, power ripple <=

50mV

• Package type: QFNWB3*3-20L(P0.4T0.55)

Application

For products such as bracelets and watches, the TP size is recommended to be within 1.8 inches.

References

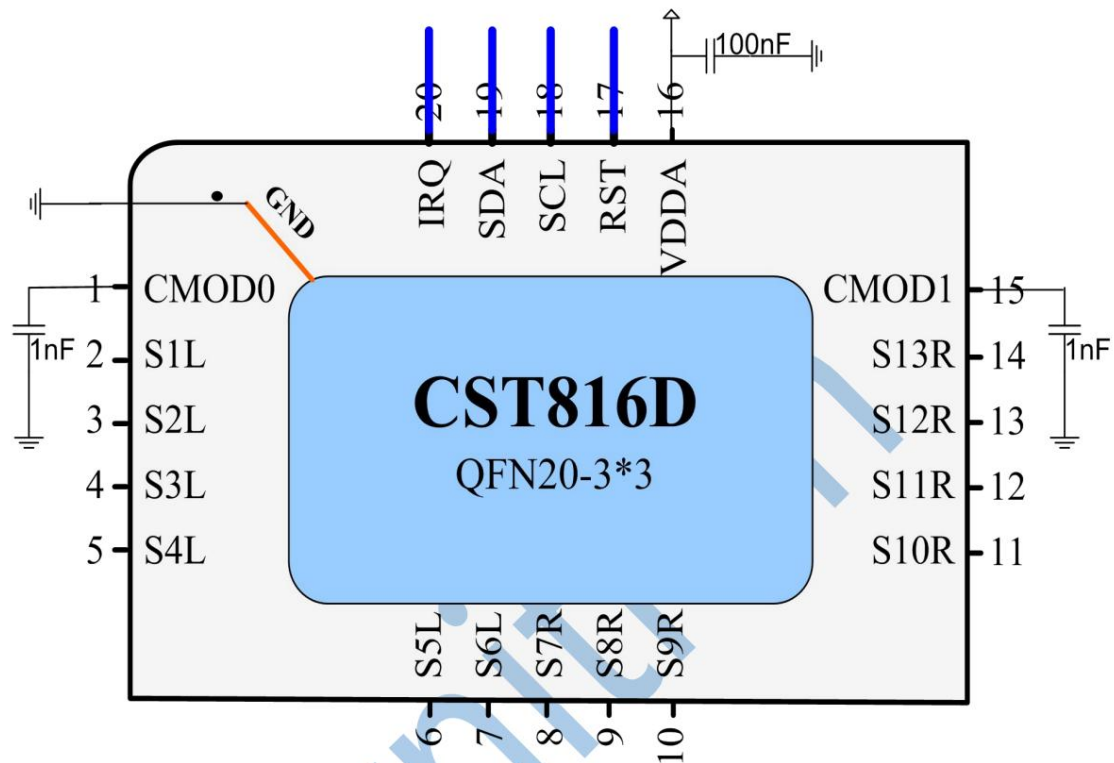


figure 1. Reference Circuit Diagram

Precautions:

• CMOD filter capacitors use NPO/COG material capacitors with at least 10% accuracy

• The selection range of CMOD capacitance value is between 1nF and 5.6nF, and 1nF is generally selected. The specific optimal value is related to the corresponding body capacitance.

• The CMOD filter capacitor must be placed close to the corresponding pin of the chip, and the trace between the capacitor and the chip should be as short as possible.



Ordering Information

Part No	Encapsulation	Surface printing	Package
CST816D	QFNWB3*3-20L(P0.4T0.55ÿ	CST816D XXXXXXXX (Production tracking code)	Taping (5000)

surface 1: Ordering Information

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Pinout/Description

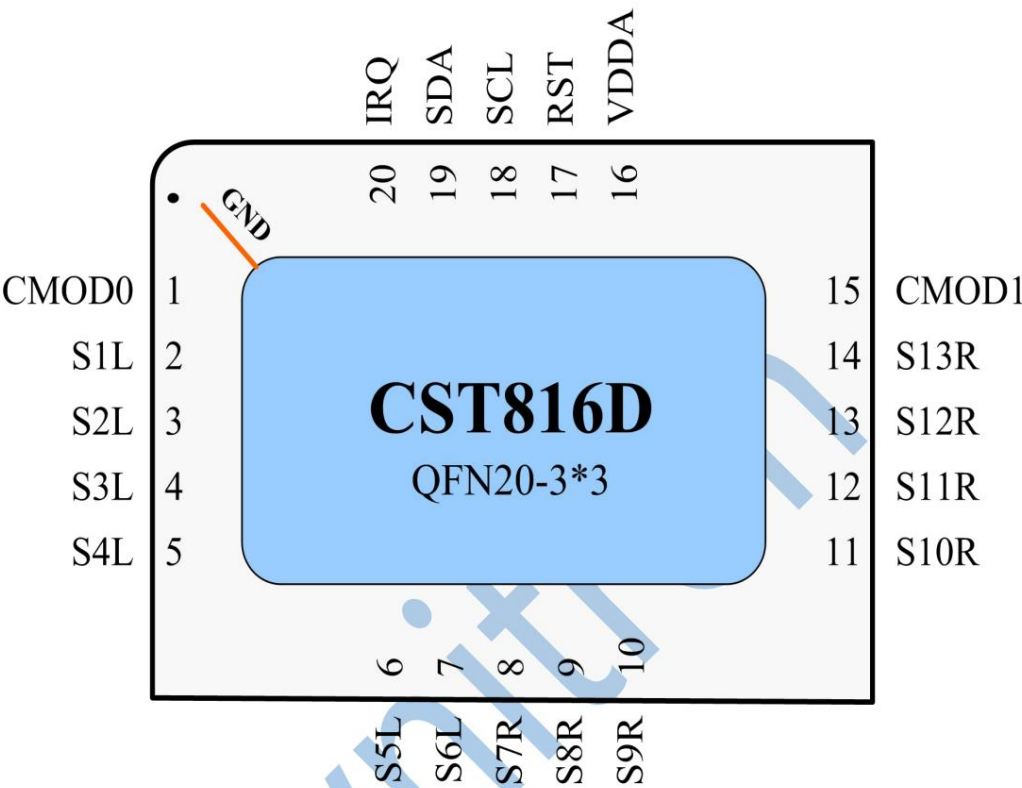


figure 2. Pin Description

name		Remark
S01~S13	Description Sensing channel	
VDDA	power supply	2.8V~3.6V, connect 2.2uF~10uF capacitor
CMOD0/CMOD1 voltage stabilizing capacitor		Connect 1nF~5.6nF voltage stabilizing capacitor
IRQ	Interrupt output	Rising/falling edge selectable
SCL/SDA	I2C	Selectable internal pull-up/open-drain mode
RST	Reset input	Low effective

surface2: Pin Description Table

Remark:

1. CMOD0/CMOD1 must be connected to a voltage stabilizing capacitor with a value between 1nF and 5.6nF;



Functional Description

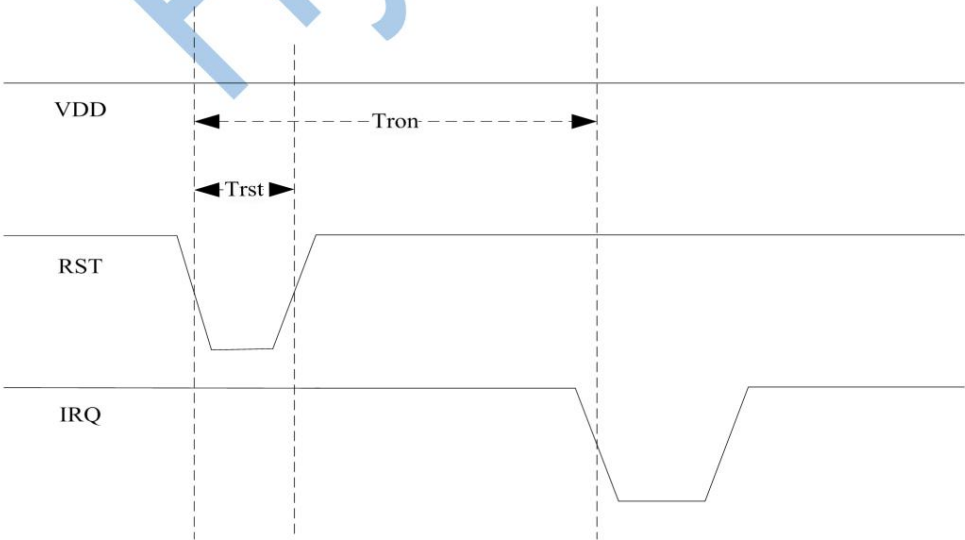
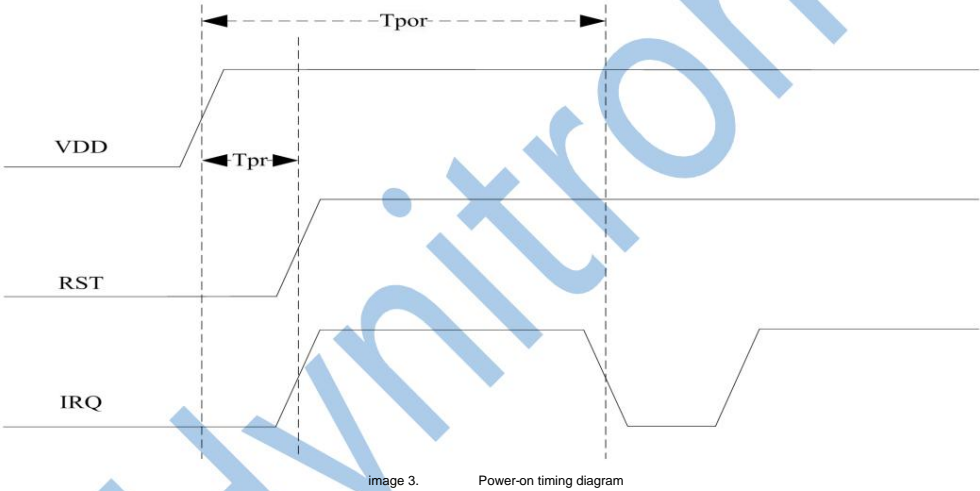
CST816D self-capacitive touch chip, through its built-in fast self-capacitive sensing module, does not require any external devices (except circuit bypass capacitors).
It can realize single-point gesture and real two-point function on patterns such as triangles; while achieving fast response, it has extremely excellent noise and anti-water, low power consumption performance.

Power on and reset

The chip has a built-in power-on reset circuit, so there is no need to connect a dedicated reset circuit externally.

The built-in power-on reset module will keep the chip in reset state until the voltage is normal. When the voltage is lower than a certain threshold, the chip will also be reset.

When the external reset pin RST is low, the entire chip will be reset. This pin can be left floating.





symbol	describe	Minimum	Maximum	Unit
Tpor	Chip initialization time after power-on	100		mS
Tpr	RST pin high delay time	5		mS
Tron	Chip reinitialization time after reset	100		mS
Trst	reset pulse time	0.1		mS

surface 3: Power-on and reset timing description

Operating mode

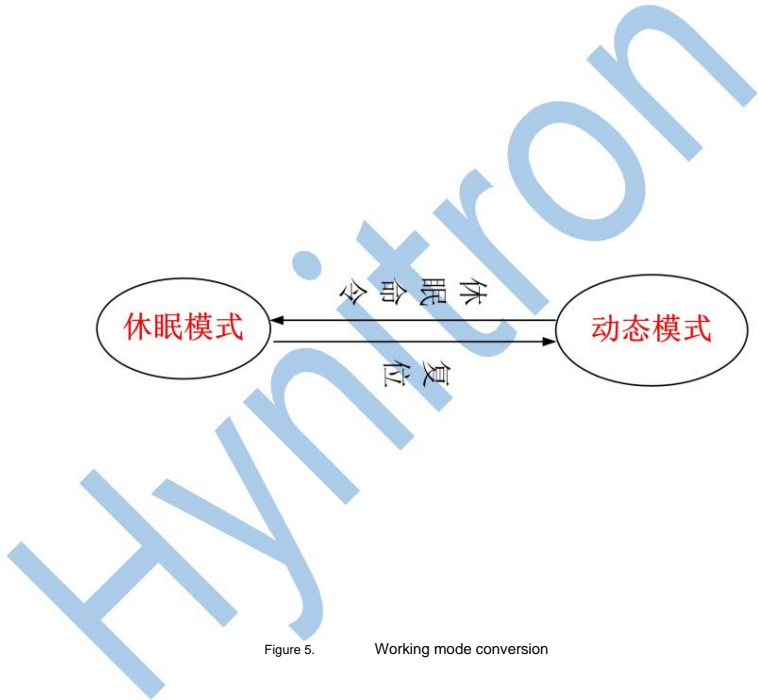


Figure 5. Working mode conversion

Dynamic Mode

When there are frequent touch operations, it is in this mode; in this mode, the touch chip quickly scans the self-capacitance of the touch screen and detects touch and report to the host.

After no touch for 2S, it will automatically enter standby mode. The function of automatically entering standby mode can be controlled by registers.

Sleep mode

After receiving the sleep command, it is in this mode; in this mode, the touch chip is in a deep sleep state to save power consumption to the maximum extent.

It can be switched to dynamic mode via the reset pin.

Channel/Node Configuration

Each channel of the CST816D self-capacitive touch chip can support self-capacitive scanning without external devices.

The self-capacitance range supported by each channel is: 1pF ~ 400pF

I2C Communication

The chip supports the standard I2C communication protocol and can achieve configurable communication rates from 10KHz to 400KHz.

The two I2C pins SCL and SDA support both open-drain mode and internal pull-up mode for flexible selection.

Interrupt mode

The touch chip will notify the host to read valid data through the IRQ pin only when it detects a valid touch and needs to report it to the host.

High efficiency, reducing CPU burden;

The interrupt edge can be configured as rising edge or falling edge as needed;

The IRQ pin is also used to wake up the host when matching a predefined gesture in standby mode.

IIC Interface Description

The chip itself supports IIC operation, and can also use IIC pins to implement simple IO operations. Specific functions can be automatically configured by software according to specific projects definition.

a) IIC address of the device

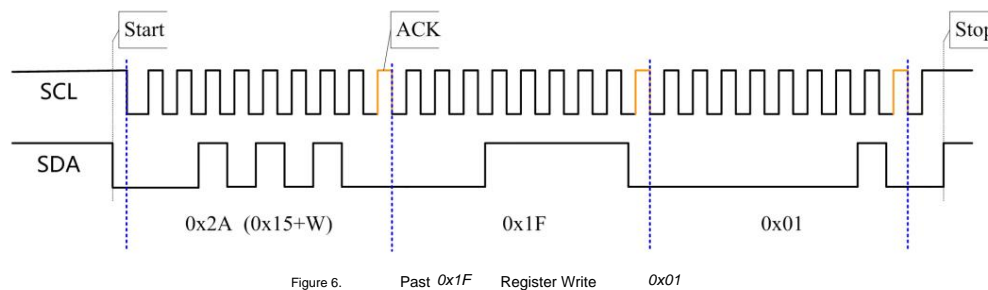
The 7-bit device address of the chip is generally 0x15, that is, the device write address is 0x2A and the read address is 0x2B.

The device addresses of some projects may be different, please consult the corresponding projects and engineering personnel.

b) IIC communication speed

In order to ensure the reliability of communication, a maximum communication rate of 400Kbps is recommended.

c) Write a single byte



d) Write multiple bytes continuously

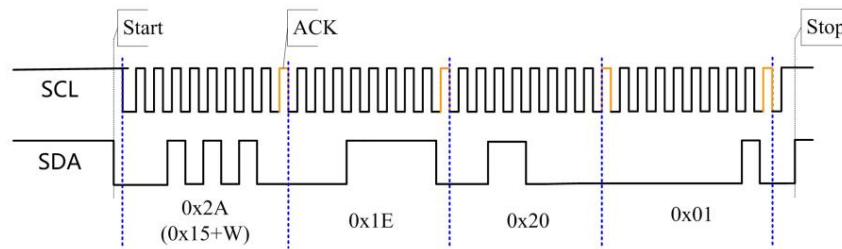


Figure 7. Past 0x1E, 0x1F Write separately 0x20, 0x01

e) Read a single byte

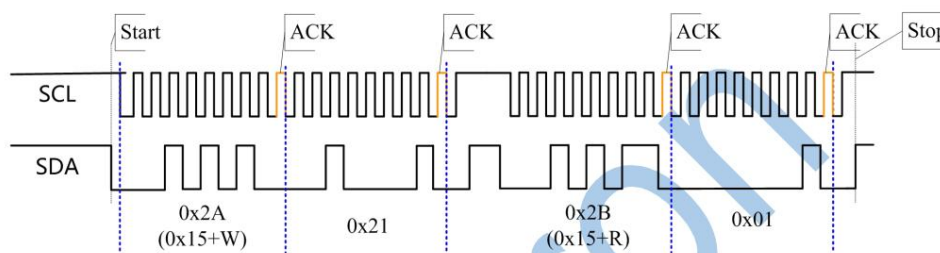


Figure 8. from 0x21 Reading a single byte

f) Read multiple bytes continuously

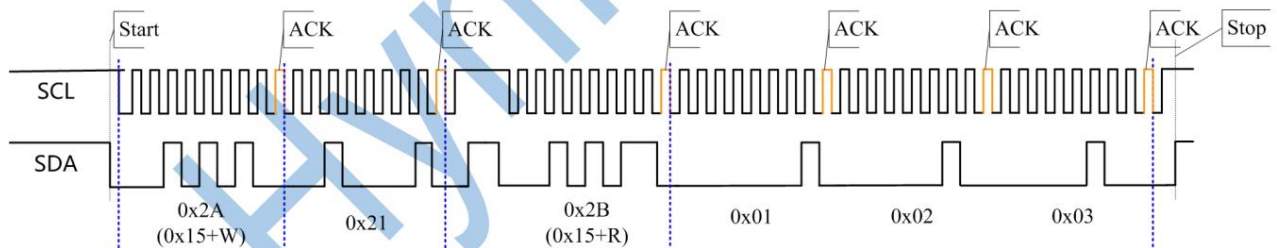


Figure 9. from 0x21, 0x22, 0x23 Read 3 Bytes

g) Timing Description

symbol	illustrate	Min	Typ	Max	Unit
F SCL _{I2C}	I2C Clock Frequency	10		400	kHz
t HDSTA _{I2C}	Hold time (repeated) START condition. After this period of time, the first Clock pulses	0.6			us
t LOW _{I2C}	The low period of the SCL clock	1.3			us
t HIGH _{I2C}	High period of SCL clock	0.6			us
tSUSTA _{I2C} Repeated START condition setup time	0.6 tSUDAT _{I2C} Data setup time				us
		100			ns
t SUSTO _{I2C}	STOP condition setup time	0.6			us
t BUFI _{I2C}	The total time between STOP and START conditions Line Idle Time	4.5			us

surface 4: IIC Timing Description

Application Design Specifications**Power supply decoupling capacitor**

Generally, a 0.1 μ F and 10 μ F ceramic capacitor connected in parallel to the VDD and VSS terminals of the chip can play the role of decoupling and bypassing. The decoupling capacitor should be placed as close to the chip as possible to minimize the current loop area.

CMOD filter capacitor

The filter capacitor uses NPO/COG material capacitors with at least 10% accuracy. The capacitance value range is between 1nF and 5.6nF, and 1nF is generally selected. The specific optimal value is related to the corresponding body capacitance. The CMOD filter capacitor must be placed close to the corresponding pin of the chip, and the trace between the chip should be as short as possible.

Waterproof precautions

There should not be large solid areas around the sensor and its wiring. Large areas of ground must be broken up.

ESD Considerations

The design of FPC will directly affect the effect of ESD. When designing, the following points must be noted: γ FPC should be fully shielded with magnetic film as much as possible, and the magnetic film must be grounded. γ The pressure and position of FPC and Sensor should be as far away from the gap of the assembly mechanism as possible to reduce the impact of ESD. γ Consider adding a TVS tube to the ground at the power supply access point to enhance the anti-ESD interference performance.

Electromagnetic Interference Considerations

Sensor routing must be isolated from lines that may cause interference, such as power routing, audio lines, LCD driver lines, Bluetooth antennas, RF antennas, etc. In particular, when TP adopts a full-fit design, it may be interfered by LCD, and the parameters of TP need to be specially debugged.

Ground

The high-precision detection circuit inside the touch chip is sensitive to the ground line. If possible, the user should use star grounding to isolate the noise of other chips. At the same time, insert magnetic beads in the grounding as much as possible to enhance the anti-interference ability. If star grounding is difficult to achieve, the user should also try to separate the ground of the high-current device from the ground of the touch chip.



Electrical characteristics

Absolute Maximum Parameters

symbol	illustrate	Min	Typ	Max	Unit
TSTG storage temperature		-40		25	°C
Ta Operating environment temperature when powered on		-20		85	°C
Vdd supply voltage relative to Vss		-0.3		+3.6	V
Vio DC input voltage		VSS-0.3		VDD+0.3	V
LU Latch-up Current				200	mA

surface 5:

Absolute Maximum Parameters

AC electrical properties Ambient temperature 25°C VDDA=3.3V

(symbols)	illustrate	Min	Typ	Max	Unit
Fcpu CPU frequency		-2%		20	MHz
F32k internal low-speed clock frequency		-5%		32	kHz
txRST external reset pulse width				0.1	ms
tPOWERUP time from POR end to CPU code execution				4	ms
FGPIO GPIO switching frequency				2	MHz
tRISE pin level rise time, Cload=50pF tFAIL pin level fall time,				32	ns
Cload=50pF				11.2	ns

surface 6:

AC electrical characteristics

DC electrical properties Ambient temperature 25°C VDDA=3.3V

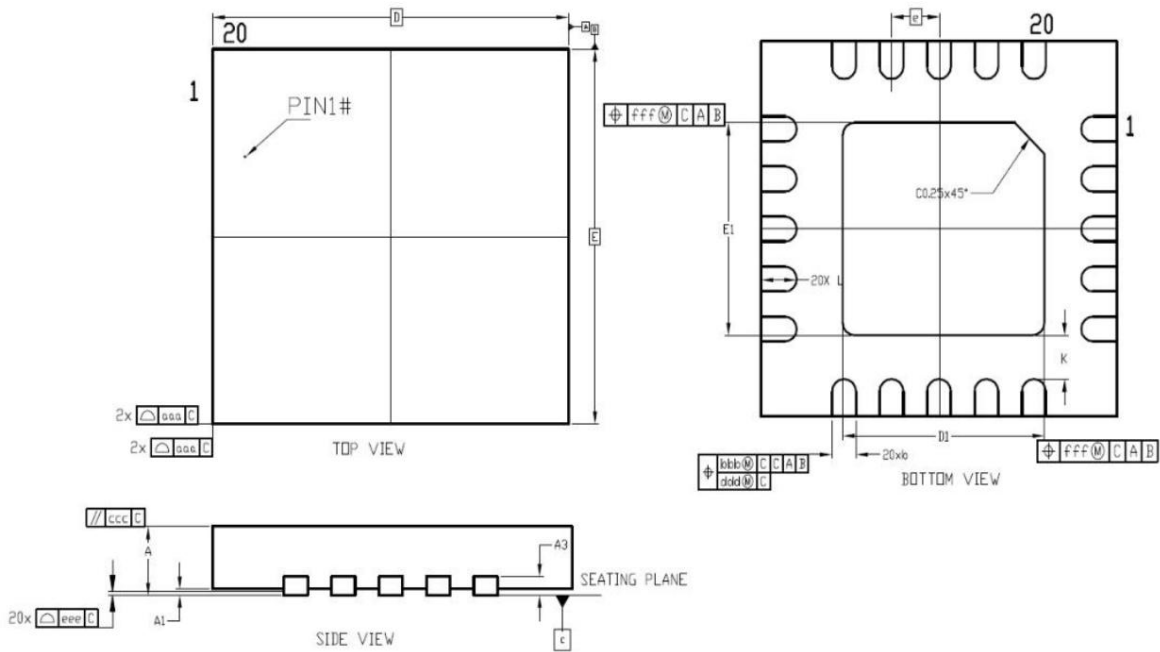
(symbols)	illustrate	Min	Typ	Max	Unit
Vdd supply voltage		2.8		3.0	V
Rpu pull-up resistor				5	kΩ
Voh high level output voltage		0.7*Vdd			V
Vol low level output voltage				0.3*Vdd	V
Ioh high level output current				2.0	mA
Iol low level sink current				20.0	mA
Vil input low level voltage				0.3*Vdd	V
Vih input high level voltage		0.7*Vdd			V
Iil input leakage current				10	nA
Idd1 operating current (dynamic mode)				4.0	mA
Idd3 operating current (sleep mode)				8.0	uA
Vddp programming voltage		2.8		3.6	V

surface 7:

DC electrical characteristics



Product Packaging



QFN20 外形图

SYMBOL	Dim	Min.	NAME.	MAX.
A		0.50	0.55	0.60
A1		0	0.02	0.05
A3			0.152 REF	-
b		0.15	0.20	0.25
D			3.00BSC	
AND			3.00BSC	
D2		1.60	1.70	1.80
E2		1.60	1.70	1.80
It is			0.40BSC	
L		0.25	0.30	0.35
K		0.20	-	-
aaa			0.10	
bbb			0.07	
ccc			0.10	
ddd			0.05	
eee			0.08	
fff			0.10	

surface 8: QFN20 Dimensions



revise history

版本	修订内容
V1.0	初始发行

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statement

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